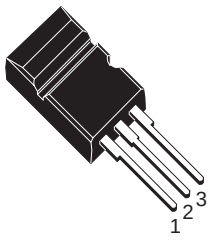
STU7NB100

N - CHANNEL 1000V - 1.2Ω - 7.3A - Max220 PowerMESH™ MOSFET

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STU7NB100	1000 V	< 1.5 Ω	7.3 A

- TYPICAL $R_{DS(on)}$ = 1.2 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- GATE CHARGE MINIMIZED
- REDUCED VOLTAGE SPREAD

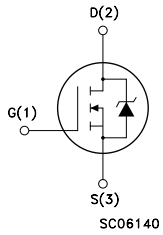


Max220

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest RDS(on) per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY AND MOTOR DRIVE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	1000	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	1000	V
V_{GS}	Gate-source Voltage	± 30	V
I_D	Drain Current (continuous) at T_c = 25 °C	7.3	A
I_D	Drain Current (continuous) at T_c = 100 °C	4.7	A
I_{DM}(•)	Drain Current (pulsed)	29	A
P_{tot}	Total Dissipation at T_c = 25 °C	160	W
	Derating Factor	1.28	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4	V/ns
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤7.3 A, di/dt ≤ 200 A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.78	$^oC/W$
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	62.5	$^oC/W$
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.5	$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose		300	^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	7.3	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 ^oC, $I_D = I_{AR}$, V_{DD} = 50 V)	600	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	1000			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_c = 125 ^oC			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 4 A		1.2	1.5	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	7.3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 4 A		8.9		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		2900 275 27		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 500 V I_D = 3.5 A R_G = 4.7 Ω V_{GS} = 10 V		32 13		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 800 V I_D = 7 A V_{GS} = 10 V		68 16 31	95	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 800 V I_D = 7 A R_G = 4.7 Ω V_{GS} = 10 V		32 32 40		ns ns ns

SOURCE DRAIN DIODE

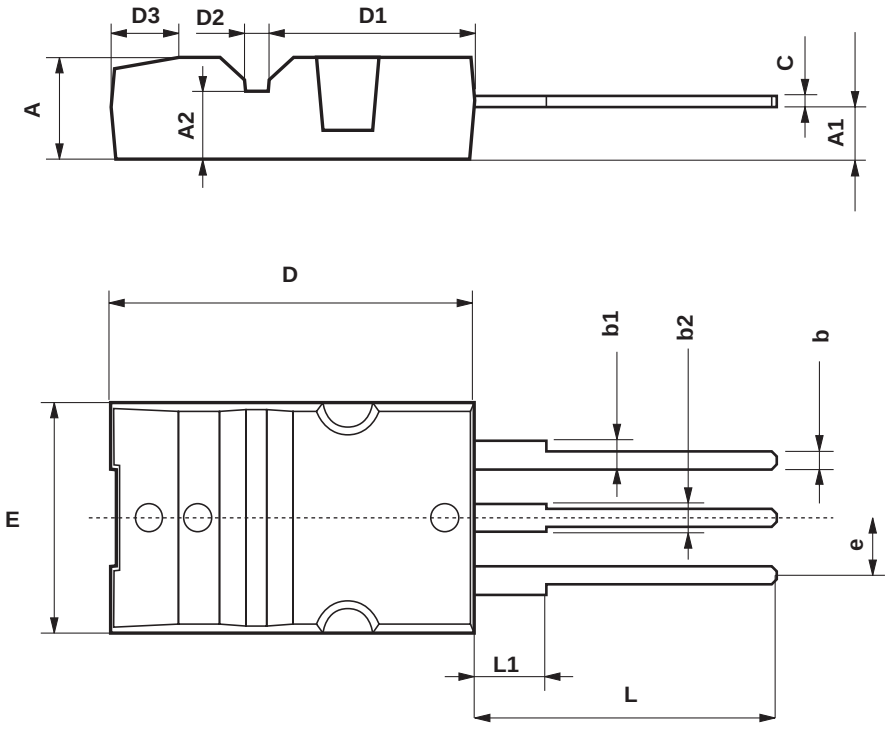
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				7.3 29	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 7.3 A V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 7 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		1000 11 21		ns µC A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

Max220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.2		2.4	0.087		0.094
A2	2.9		3.1	0.114		0.122
b	0.7		0.93	0.027		0.036
b1	1.25		1.4	0.049		0.055
b2	1.2		1.38	0.047		0.054
c	0.45		0.6		0.18	0.023
D	15.9		16.3		0.626	0.641
D1	9		9.35	0.354		0.368
D2	0.8		1.2	0.031		0.047
D3	2.8		3.2	0.110		0.126
e	2.44		2.64	0.096		0.104
E	10.05		10.35	0.396		0.407
L	13.2		13.6	0.520		0.535
L1	3		3.4	0.118		0.133



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